LPM9014

N-Channel Enhancement Mode Field Effect Transistor

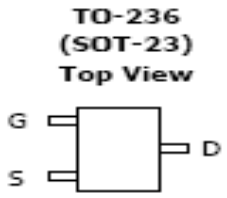
General Description

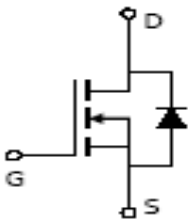
The LPM9014 uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. *Standard Product LPM9014 is Pb-free (meets ROHS & Sony 259 specifications). LPM9014L is a Green Product ordering option. LPM9014 and LPM9014L are electricallv identical.*

Features

VDS (V) = 20V
ID = 4.2A
RDS(ON) < 50mΩ (VGS = 4.5V)
RDS(ON) < 63mΩ (VGS = 2.5V)
RDS(ON) < 87mΩ (VGS = 1.8V)

Pin Configurations





Absolute Maximum Ratings T_A=25°C unless otherwise noted				
Parameter		**Symbol**	**Maximum**	**Units**
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current [A]	T_A=25°C	I_D	4.2	A
	T_A=70°C		3.2	
Pulsed Drain Current [B]		I_{DM}	15	
Power Dissipation [A]	T_A=25°C	P_D	1.4	W
	T_A=70°C		0.9	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics					
Parameter		**Symbol**	**Typ**	**Max**	**Units**
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	70	90	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		100	125	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	63	80	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=16V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±8V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	0.4	0.6	1	V
$I_{D(ON)}$	On state drain current	V_{GS}=4.5V, V_{DS}=5V	15			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=4.5V, I_D=4.2A		41	50	mΩ
		T_J=125°C		58	70	
		V_{GS}=2.5V, I_D=3.7A		52	63	mΩ
		V_{GS}=1.8V, I_D=3.2A		67	87	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=4.2A		11		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.76	1	V
I_S	Maximum Body-Diode Continuous Current				2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=10V, f=1MHz		436		pF
C_{oss}	Output Capacitance			66		pF
C_{rss}	Reverse Transfer Capacitance			44		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		3		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=10V, I_D=4.2A		6.2		nC
Q_{gs}	Gate Source Charge			1.6		nC
Q_{gd}	Gate Drain Charge			0.5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=5V, V_{DS}=10V, R_L=2.7Ω, R_{GEN}=6Ω		5.5		ns
t_r	Turn-On Rise Time			6.3		ns
$t_{D(off)}$	Turn-Off DelayTime			40		ns
t_f	Turn-Off Fall Time			12.7		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=4A, dI/dt=100A/µs		12.3		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=4A, dI/dt=100A/µs		3.5		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80µs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

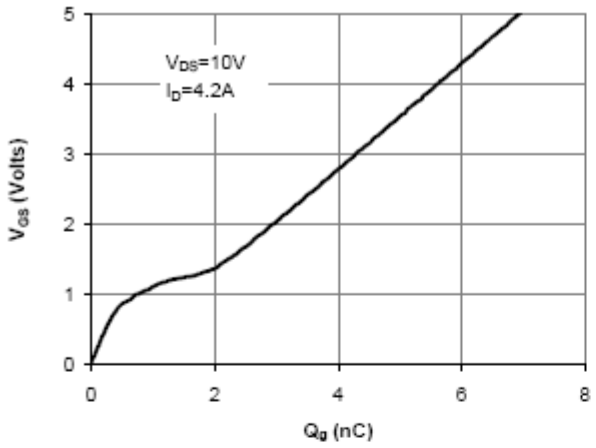


Figure 7: Gate-Charge Characteristics

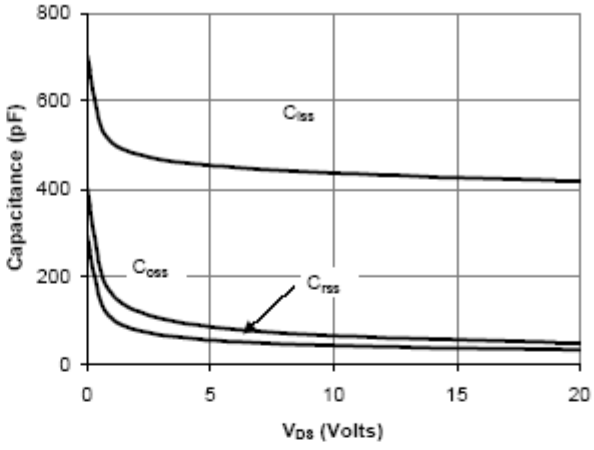


Figure 8: Capacitance Characteristics

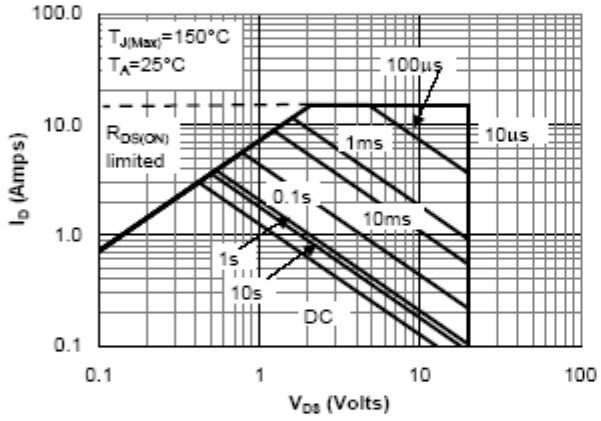


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

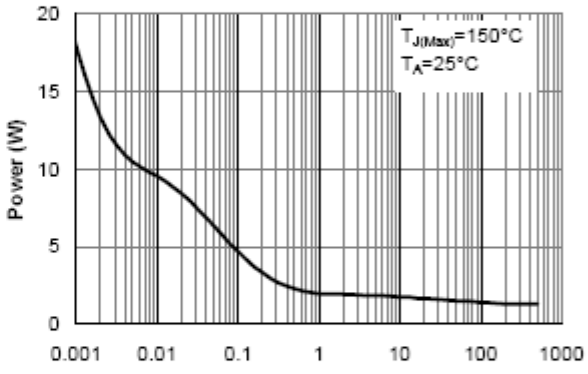


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

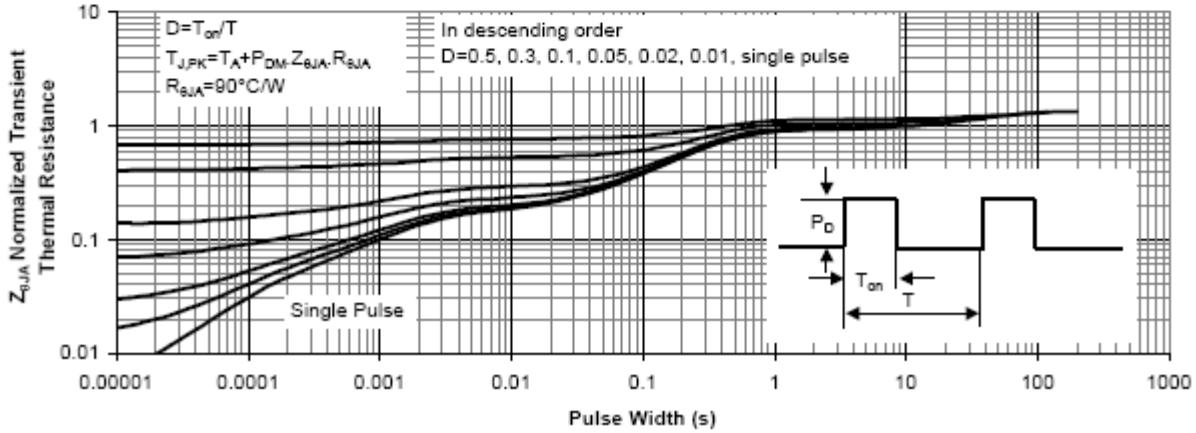


Figure 11: Normalized Maximum Transient Thermal Impedance